

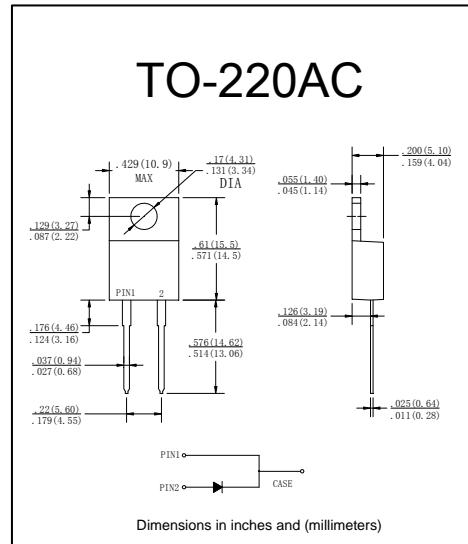


超快恢复整流二极管 Ultra-Fast Recovery Rectifier Diodes

■ 特征 Features

- I_o 16.0A
- V_{RRM} 200V
- 玻璃钝化芯片 Glass passivated chip
- 耐正向浪涌电流能力高
High surge forward current capability

■ 外形尺寸和印记 Outline Dimensions and Mark



■ 用途 Applications

- 快速整流用
High speed switching

■ 极限值 (绝对最大额定值)

Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions	MUR1620
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		200
平均整流输出电流 Average Rectified Output Current	I_o	A	正弦半波 60Hz, 电阻负载, T_c (Fig.1) 60Hz Half-sine wave, Resistance load, T_c (Fig.1)	16
正向(不重复)浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz正弦波, 一个周期, $T_a=25^\circ C$ 60Hz sine wave, 1 cycle, $T_a=25^\circ C$	200
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	I^2t	A^2s	$1ms \leq t < 8.3ms$ $T_j=25^\circ C$	167
贮存温度 Storage Temperature	T_{stg}	°C		-55 ~ +150
结温 Junction Temperature	T_j	°C		-55 ~ +175

■ 电特性 ($T_a=25^\circ C$ 除非另有规定)Electrical Characteristics ($T_a=25^\circ C$ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition		最大值 Max
正向峰值电压 Peak Forward Voltage	V_{FM}	V	$I_{FM}=16.0A$		0.975
反向峰值电流 Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$	$T_a=25^\circ C$	10
	I_{RRM2}			$T_a=125^\circ C$	500
反向恢复时间 Reverse Recovery Time	T_{rr}	ns	$I_F=0.5A$ $I_{RM}=1A$ $I_{RR}=0.25A$		50
热阻 Thermal Resistance	$R_{\theta J-C}$	°C/W	结和壳之间 Between junction and case		2.0



■特性曲线(典型) Characteristics(Typical)

图1: 正向电流降额曲线
FIG1: IF (AV) --T_c Derating

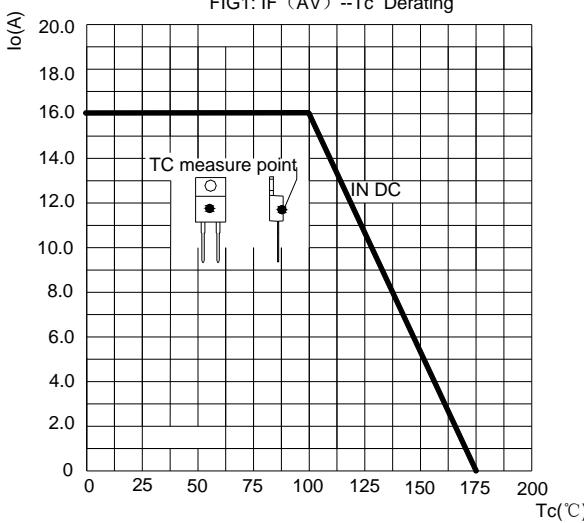


图2: 耐正向浪涌电流曲线
FIG2: Surge Forward Current Capability

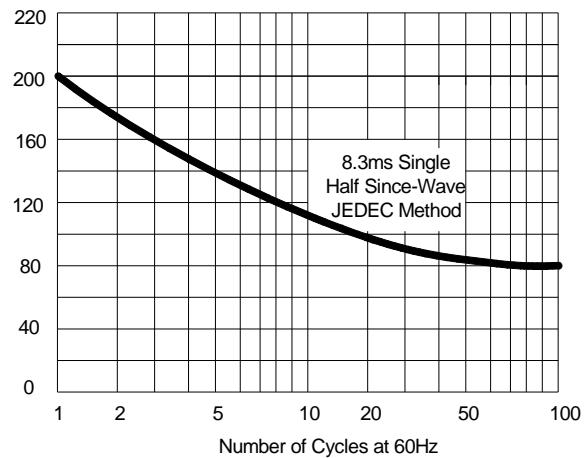


图3: 正向电压曲线

FIG3: Instantaneous Forward Voltage

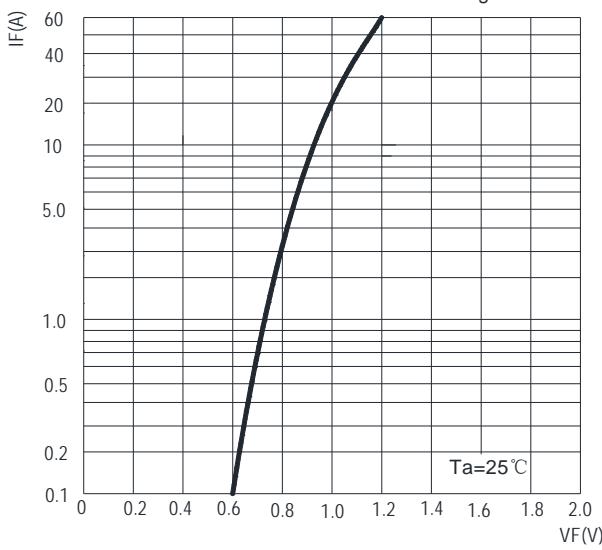


图4: 反向电流曲线

FIG4: Typical Reverse Characteristics

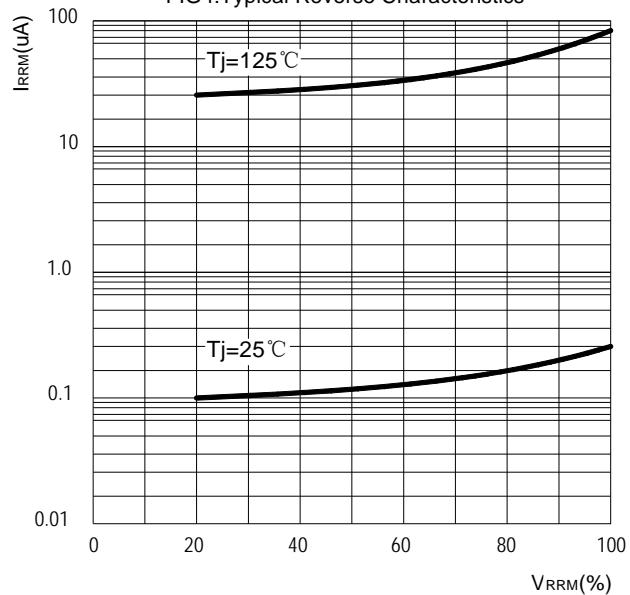


图5: 反向恢复时间试验电路及测试波形示意图
Diagram of circuit and Testing wave form of reverse recovery time

